

#7/Amata  
PATENT  
11/16/02

Docket No.: 57454-178

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of

Shoichiro NAKAZAWA, et al.

Serial No.: 09/915,567

Group Art Unit: 2822

Filed: July 27, 2001

Examiner: I.M. Soward

For: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE  
SAME

**AMENDMENT**

Commissioner for Patents  
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office

Action dated August 14, 2002.

**IN THE TITLE:**

Please delete the title [SEMICONDUCTOR DEVICE AND METHOD OF  
MANUFACTURING THE SAME] and insert the following new title: --METHOD OF  
MANUFACTURING A SEMICONDUCTOR DEVICE--

**IN THE SPECIFICATION:**

Page 1; please amend the paragraph commencing at line 20 as follows:

When there is a gap of a high aspect ratio between transfer gates as described  
above, at the time of forming an insulating layer, the gap between the transfer gates

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